



**FEATURES**

Power dissipation

$$P_{CM} : 0.5 \text{ W (Tamb=25°C)}$$

Collector current

$$I_{CM} : 1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 100 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$

**DEVICE MARKING**

BCX56=BH

BCX56-10=BK

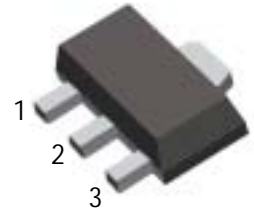
BCX56-16=BL

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100 \mu A, I_E=0$	100		V	
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	80		V	
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10 \mu A, I_C=0$	5		V	
Collector cut-off current	$I_{CBO}$	$V_{CB}=30V, I_E=0$		0.1	$\mu A$	
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$		0.1	$\mu A$	
DC current gain	<b>BCX56</b> <b>BCX56-10</b> <b>BCX56-16</b>	$h_{FE(1)}$	$V_{CE}=2V, I_C=150mA$	63 63 100	250 160 250	
		$h_{FE(2)}$	$V_{CE}=2V, I_C=5mA$	40		
		$h_{FE(3)}$	$V_{CE}=2V, I_C=500mA$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.5	V	
Base-emitter voltage	$V_{BE(ON)}$	$I_C=500mA, V_{CE}=2V$		1	V	
Transition frequency	$f_T$	$V_{CE}=5V, I_C=1mA$ $f=100MHz$	130		MHz	